

ABSTRACT OF THE DISCLOSURE

The present invention solves the problem of conventional group-III nitride semiconductor LED in that, since the LED driving current is supplied only from a pad electrode serving also as an ohmic electrode, the driving current cannot
5 diffuse over a wide range of the light-emitting region and a group-III nitride semiconductor LED having high light emission intensity cannot be successfully provided. A group-III nitride semiconductor LED having high light emission intensity, which is fabricated using a stacked layer structure obtained by providing a surface ohmic electrode, a window layer including an electrically
10 conducting transparent oxide crystal layer and a pad electrode on an electrically conducting substrate through a boron phosphide (BP)-based buffer layer to allow the driving current to diffuse over a wide range of the light-emitting region is provided.

09881782-061801